

### 2ED020I12FA

# Dual IGBT Driver IC SP001054678





### 1 Overview

### **Main Features**

- Dual channel isolated IGBT Driver
- For 600V/1200V IGBTs
- 2 A rail-to-rail output
- Vcesat-detection
- Active Miller Clamp

### **Product Highlights**

- Coreless transformer isolated driver
- Basic insulation according to DIN EN 60747-5-2
- Basic insulation recognized under UL 1577
- Integrated protection features
- · Suitable for operation at high ambient temperature
- AEC Qualified

### **Typical Application**

- Drive inverters for HEV and EV
- Auxiliary inverters for HEV and EV
- High Power DC/DC inverters

### Description

The 2ED020I12FA is a galvanic isolated dual channel IGBT driver in PG-DSO-36 package (32 pins) that provides two fully independent driver outputs with a current capability of typically 2A.

All logic pins are 5V CMOS compatible and could be directly connected to a microcontroller.

The data transfer across galvanic isolation is realized by the integrated Coreless Transformer Technology.

The 2ED020I12FA provides several protection features like IGBT desaturation protection, active Miller clamping and active shut down.

Туре	Package	Marking
2ED020I12FA	PG-DSO-36	2ED020I12FA





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Block Diagram



## 2 Block Diagram

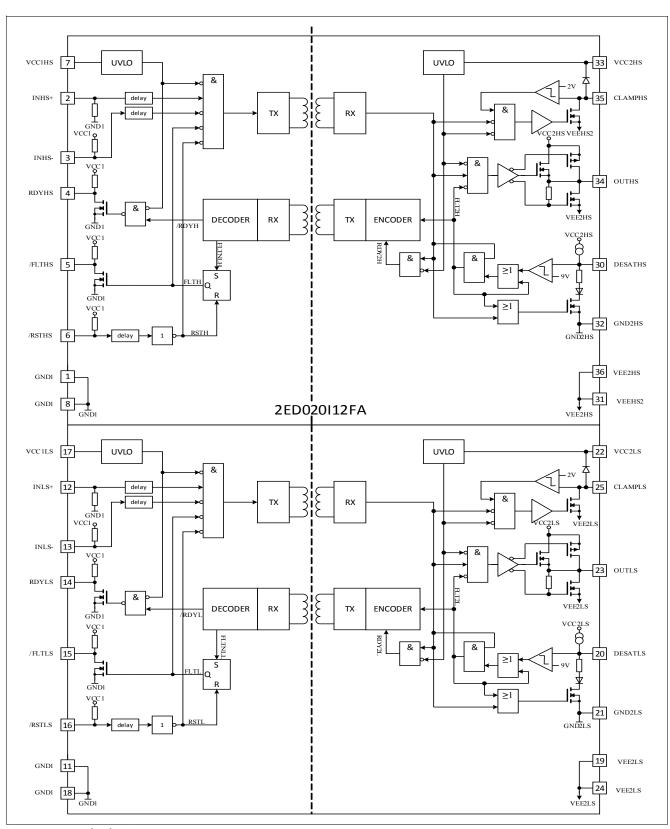


Figure 1 Block Diagram 2ED020I12FA

## **Dual IGBT Driver IC**



Pin Configuration and Functionality

### Pin Configuration and Functionality 3

#### 3.1 **Pin Configuration**

#### Pin Configuration Table 1

Pin	Name	Function
No.		
1	GND1	Common ground input side
2	INHS+	Non inverted driver input high side
3	INHS-	Inverted driver input high side
4	RDYHS	Ready output high side
5	/FLTHS	Inverted fault output high side
6	/RSTHS	Inverted reset input high side
7	VCC1HS	Positive power supply input high side
8	GND1	Common ground input side
9	NC	Not used, internally connected to Pin 10
10	NC	Not used, internally connected to Pin 9
11	GND1	Common ground input side
12	INLS+	Non inverted driver input low side
13	INLS-	Inverted driver input low side
14	RDYLS	Ready output low side
15	/FLTLS	Inverted fault output low side
16	/RSTLS	Inverted reset input low side
17	VCC1LS	Positive power supply input low side
18	GND1	Common ground input side
19	VEE2LS	Negative power supply low side driver
20	DESATLS	Desaturation protection low side driver
21	GND2LS	Signal ground low side driver
22	VCC2LS	Power supply low side driver
23	OUTLS	Output low side driver
24	VEE2LS	Negative power supply low side driver
25	CLAMPLS	Miller clamping low side driver
26		Pin not existing, cut out
27		Pin not existing, cut out
28		Pin not existing, cut out
29		Pin not existing, cut out
30	DESATHS	Desaturation protection high side driver
31	VEE2HS	Negative power supply high side driver



### Pin Configuration and Functionality

**Table 1 Pin Configuration** (cont'd)

Pin No.	Name	Function
32	GND2HS	Signal ground high side driver
33	VCC2HS	Power supply high side driver
34	OUTHS	Output high side driver
35	CLAMPHS	Miller clamping high side driver
36	VEE2HS	Negative power supply high side driver

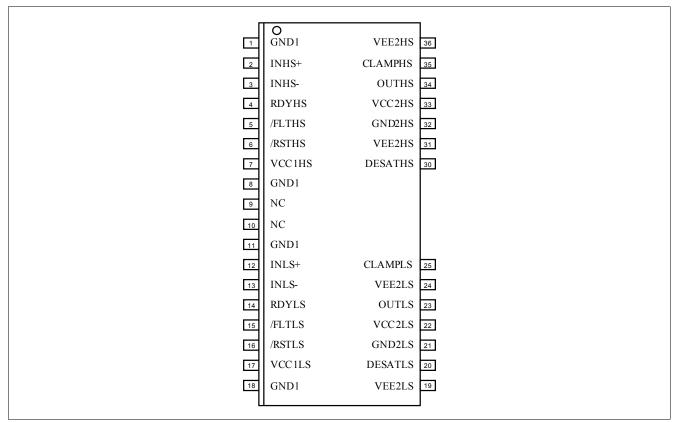


Figure 2 PG-DSO-36 (top view)

### 3.2 Pin Functionality

Remark: xxxHS and xxxLS at the end of pin name only indicates an order for description, both drivers are isolated and could be used as high side or low side without any preference.

### **GND1**

Common ground connection of the input side.

### INHS+, INLS+ Non Inverting Driver Input

Positive control signal for the driver output (see Figure 6).

A minimum pulse width is defined to make the IC robust against glitches at IN+. An internal pull-down-resistor ensures IGBT off-state.

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### Pin Configuration and Functionality

### INHS-, INLS- Inverting Driver Input

Negative control signal for the driver output (see Figure 6)..

A minimum pulse width is defined to make the IC robust against glitches at INxx-. An internal pull-up-resistor ensures IGBT off-state.

### /RSTHS, /RSTLS Reset Input

**Function 1:** Enable/shutdown of the input chip (The IGBT is off if /RSTxx = low). A minimum pulse width is defined to make the IC robust against glitches at /RSTxx.

**Function 2:** Resets the DESAT-FAULT-state of the chip if /RSTxx is low for a time  $T_{RST}$ . An internal pull-upresistor is used to ensure /FLTxx status output.

### /FLTHS, /FLTLS Fault Output

Open-drain output to report a desaturation error of the IGBT (/FLTxx is low if desaturation occurs).

### RDYHS, RDYLS Ready Status Output

Open-drain output to report the correct operation of the device (RDYxx = high if both chips are above the UVLO level and the internal chip transmission is faultless).

### **VCC1HS, VCC1LS Positive Supply**

5 V power supply of the input chip

### **VEE2HS, VEE2LS Negative Supply**

Negative power supply pins of the output chip. If no negative supply voltage is available, each pins has to be connected to its respective GND2xx.

### **DESATHS, DESATLS Desaturation Detection Input**

Monitoring of the IGBT saturation voltage ( $V_{CE}$ ) to detect desaturation caused by short circuits. If OUT is high,  $V_{CE}$  is above a defined value and a certain blanking time has expired, the desaturation protection is activated and the IGBT is switched off. The blanking time is adjustable by an external capacitor.

### **CLAMPHS, CLAMPLS Miller Clamping**

Ties the gate voltage to ground after the IGBT has been switched off at a defined voltage to avoid a parasitic switch-on of the IGBT. During turn-off, the gate voltage is monitored and the clamp output is activated when the gate voltage goes below V<sub>CLAMP TH</sub>.

### GND2HS, GND2LS Reference Ground

Reference ground of the output chip.

### **OUTHS, OUTLS Driver Output**

Output pin to drive an IGBT. The voltage is switched between VEE2xx and VCC2xx. In normal operating mode Vout is controlled by INxx+, INxx- and /RSTxx. During error mode (UVLO, internal error or DESATxx Vout is driven to VEE2xx independent of the input control signals.

### VCC2HS, VCC2LS Positive Supply

Positive power supply pin of the output side.

### **Functional Description**



### 4 Functional Description

### 4.1 Introduction

The 2ED020I12FA is an advanced IGBT dual gate driver that can be also used for driving power MOS devices. Control and protection functions are included to make possible the design of high reliability systems.

The device consists of two galvanic separated driver. The input can be directly connected to a standard 5 V DSP or microcontroller with CMOS in/output and the output driver are connected to the high side and low side switch.

The rail-to-rail driver outputs enables the user to provide easy clamping of the IGBTs gate voltage during short circuit of the IGBT. So an increase of short circuit current due to the feedback via the Miller capacitance can be avoided. Further, a rail-to-rail output reduces power dissipation.

The device also includes IGBT desaturation protection with FAULT status outputs.

Two READY status outputs reports if the device is supplied and operates correctly.

### 4.2 Supply

The driver 2ED020I12FA is designed to support two different supply configurations, bipolar supply and unipolar supply.

In bipolar supply the driver is typically supplied with a positive voltage of 15V at VCC2 and a negative voltage of -8V at VEE2, please refer to Figure 3. Negative supply prevents a dynamic turn on due to the additional charge which is generated from IGBT input capacitance times negative supply voltage. If an appropriate negative supply voltage is used, connecting CLAMPxx to IGBT gate is redundant and therefore typically not necessary.



### **Functional Description**

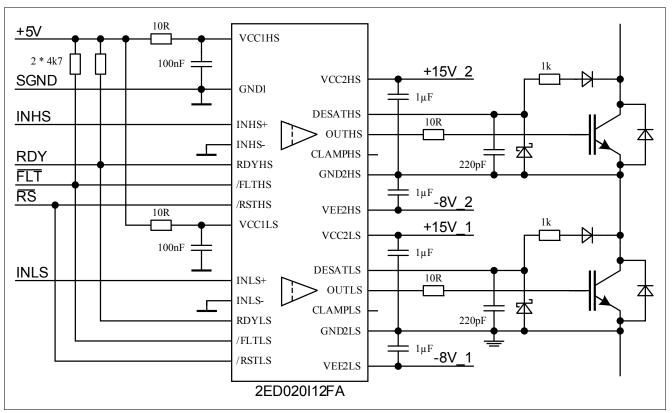


Figure 3 Application Example Bipolar Supply

For unipolar supply configuration the driver is typically supplied with a positive voltage of 15V at VCC2. Erratically dynamic turn on of the IGBT could be prevented with active Miller clamp function, so CLAMP output is directly connected to IGBT gate, please refer to Figure 4.

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### **Functional Description**

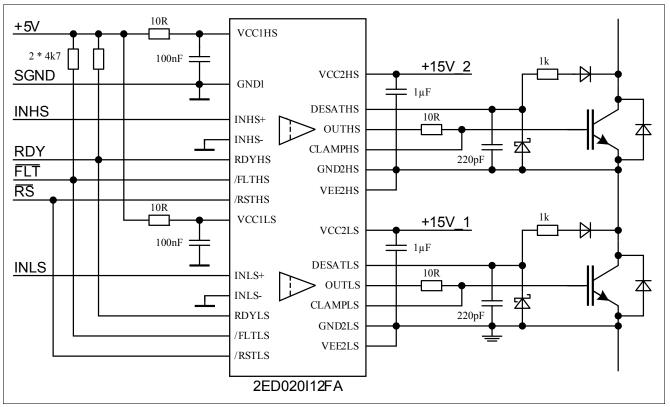


Figure 4 Application Example Unipolar Supply

### 4.3 Internal Protection Features

### 4.3.1 Undervoltage Lockout (UVLO)

To ensure correct switching of IGBTs the device is equipped with undervoltage lockout for all driver outputs as well as for input section, please see **Figure 8**.

If the power supply voltage  $V_{VCC1xx}$  of the input section drops below  $V_{UVLOL1}$  a turn-off signal is sent to the output driver before power-down. The IGBT is switched off and the signals at INxx+ and INxx- are ignored as long as  $V_{VCC1xx}$  reaches the power-up voltage  $V_{UVLOH1}$ .

If the power supply voltage  $V_{VCC2xx}$  of the output driver goes down below  $V_{UVLOL2}$  the IGBT is switched off and signals from the input chip are ignored as long as  $V_{VCC2xx}$  reaches the power-up voltage  $V_{UVLOH2}$ . VEE2xx is not monitored.

### 4.3.2 READY Status Output

The READY outputs shows the status of three internal protection features.

- UVLO of the input chip
- UVLO of the output chip after a short delay
- Internal signal transmission after a short delay

It is not necessary to reset the READY signal since its state only depends on the status of the former mentioned protection signals.

### **Functional Description**



### 4.3.3 Watchdog Timer

During normal operation the internal signal transmission is monitored by a watchdog timer. If the transmission fails for a given time, the IGBT is switched off and the READY output reports an internal error.

### 4.3.4 Active Shut-Down

The Active Shut-Down feature ensures a safe IGBT off-state if the output chip is not connected to the power supply, IGBT gate is clamped at OUTxx to VEE2xx.

### 4.4 Non-Inverting and Inverting Inputs

There are two possible input modes to control the IGBT. At non-inverting mode INxx+ controls the driver output while INxx- is set to low. At inverting mode INxx- controls the driver output while INxx+ is set to high, please see **Figure 6**. A minimum input pulse width is defined to filter occasional glitches.

### 4.5 **Driver Outputs**

The output driver sections uses only MOSFETs to provide a rail-to-rail output. This feature permits that tight control of gate voltage during on-state and short circuit can be maintained as long as the drivers supply is stable. Due to the low internal voltage drop, switching behavior of the IGBT is predominantly governed by the gate resistor. Furthermore, it reduces the power to be dissipated by the driver.

### 4.6 External Protection Features

### 4.6.1 Desaturation Protection

A desaturation protection ensures the protection of the IGBT at short circuit. When the DESAT voltage goes up and reaches V<sub>DESAT\_TH</sub>, the output is driven low. Further, the FAULT output is activated, please refer to **Figure 7**. A configurable blanking time is used to allow enough time for IGBT saturation. Blanking time is provided by a highly precise internal current source and an external capacitor.

### 4.6.2 Active Miller Clamp

In a half bridge configuration the switched off IGBT tends to dynamically turn on during turn on phase of the opposite IGBT. A Miller clamp allows sinking the Miller current across a low impedance path in this high dV/dt situation. Therefore in many applications, the use of a negative supply voltage can be avoided.

During turn-off, the gate voltage is monitored and the clamp output is activated when the gate voltage goes below  $V_{\text{CLAMP TH}}$ . The clamp is designed for a Miller current up to  $I_{\text{CLAMPL}}$ .

### 4.6.3 Short Circuit Clamping

During short circuit the IGBTs gate voltage tends to rise because of the feedback via the Miller capacitance. An additional protection circuit connected to OUTxx and CLAMPxx limits this voltage to a value slightly higher than the supply voltage. A current of maximum 500 mA for 10  $\mu$ s may be fed back to the supply through one of this paths. If higher currents are expected or a tighter clamping is desired external Schottky diodes may be added.

### 4.7 RESET

The reset inputs have two functions.



### **Functional Description**

Firstly, /RSTxx is in charge of setting back the FAULT output. If /RSTxx is low longer than a given time, /FLTxx will be cleared at the rising edge of /RSTxx; otherwise, it will remain unchanged. Moreover, it works as enable/shutdown of the input logic.

### **Electrical Parameters**



#### **Electrical Parameters** 5

#### **Absolute Maximum Ratings** 5.1

Note:

Absolute maximum ratings are defined as ratings, which when being exceeded may lead to destruction of the integrated circuit. Unless otherwise noted all parameters refer to GND1. The specification for all driver signals is valid for HS and LS with out special notice, e.g. IN+ covers INHS+ as well as INLS+. The signals from driver output side are measured with respect to their specific GND2HS or GND2LS.

Absolute Maximum Ratings 1) Table 2

Parameter	Symbol	V	alues	Unit	Note	
		Min.	Max.			
Positive power supply output side	$V_{\sf VCC2}$	-0.3	20	V	Referenced to GND2	
Negative power supply output side	$V_{VEE2}$	-12	0.3	V	Referenced to GND2	
Maximum power supply voltage output side (V <sub>VCC2</sub> - V <sub>VEE2</sub> )	$V_{max2}$	-	28	V	-	
Gate driver output	$V_{OUT}$	$V_{VEE2}$ -0.3	V <sub>VCC2</sub> +0.3	V	_	
			V <sub>VCC2</sub> + V <sub>CLPout</sub>	V	time< $t_{\rm CLPmax}$ , $I_{\rm OUT}$ <500 mA (see Table 9)	
Gate driver high output maximum current	$I_{OUT}$	-	2.4	A	t = 2 μs	
Gate & Clamp driver low output maximum current	$I_{OUT}$	-	2.4	A	t = 2 μs	
Maximum short circuit clamping time	$t_{CLP}$	-	10	μs	$I_{CLAMP/OUT} = 500 \; mA$	
Positive power supply input side	$V_{\sf VCC1}$	-0.3	6.5	V	_	
Logic input voltages	$V_{LogicIN}$	-0.3	<sub>VCC1</sub> + 0.3	V	_	
(IN+,IN-,RST)			6.5	V	-	
Opendrain Logic output voltage (FLT)	$V_{FLT\#}$	-0.3	6.5V	V	-	
Opendrain Logic output voltage (RDY)	$V_{RDY}$	-0.3	6.5V	V	-	
Opendrain Logic output current (FLT)	$I_{FLT\#}$	-	10	mA	-	
Opendrain Logic output current (RDY)	$I_{RDY}$	-	10	mA	-	
Pin DESAT voltage	$V_{DESAT}$	-0.3	V <sub>VCC2</sub> +0.3	V	Referenced to GND2	

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### **Electrical Parameters**

Table 2 Absolute Maximum Ratings (cont'd)<sup>1)</sup>

Parameter	Symbol	V	'alues	Unit	Note
		Min.	Max.		
Pin CLAMP voltage	$V_{CLAMP}$	$V_{VEE2}$ -0.3	V <sub>VCC2</sub> +0.3	V	_
		$V_{VEE2}$ -0.3	$V_{ m VCC2}$ + $V_{ m CLPclamp}$	V	time< $t_{\rm CLPmax}$ , $I_{\rm CLAMP}$ <500 mA (see Table 9)
Junction temperature	$T_{J}$	-40	150	°C	-
Storage temperature	$T_{S}$	-55	150	°C	-
Power dissipation, per input part	$P_{D,IN}$	_	100	mW	<sup>2)</sup> @T <sub>A</sub> = 25°C
Power dissipation, per output part	$P_{D,OUT}$	_	400	mW	<sup>2)</sup> @T <sub>A</sub> = 25°C
Power dissipation, total	$P_{D,tot}$	_	1000	mW	<sup>2)</sup> @T <sub>A</sub> = 25°C
Thermal resistance (Input part)	$R_{THJA,IN}$	-	375	K/W	$^{2)}$ @ $T_A$ = 25°C, $P_{D, IN\_HS+LS}$ = 200 mW, $P_{D, OUT\_HS+LS}$ = 800 mW
Thermal resistance (Output part)	$R_{THJA,OUT}$	-	110	K/W	$^{2)}$ @ $T_{A}$ = 25°C, $P_{D, IN\_HS+LS}$ = 200 mW, $P_{D, OUT\_HS+LS}$ = 800 mW
ESD Capability	$V_{ESD}$	_	1	kV	Human Body Model <sup>3)</sup>

<sup>1)</sup> Not subject to production test. Absolute maximum Ratings are verified by design / characterization

<sup>2)</sup> IC power dissipation is derated linearly at 12 mW/°C above 65°C. Thermal performance may change significantly with layout and heat dissipation of components in close proximity.

<sup>3)</sup> According to EIA/JESD22-A114-B (discharging a 100 pF capacitor through a 1.5 k $\Omega$  series resistor).

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### **Electrical Parameters**

### 5.2 Operating Parameters

Note:

Within the operating range the IC operates as described in the functional description. Unless otherwise noted all parameters refer to GND1. The specification for all driver signals is valid for HS and LS with out special notice, e.g. IN+ covers INHS+ as well as INLS+. The signals from driver output side are measured with respect to their specific GND2HS or GND2LS.

Table 3 Operating Parameters

Parameter	Symbol	Values		Unit	Note
		Min.	Max.		
Positive power supply output side	$V_{\sf VCC2}$	13	20	V	referenced to GND2
Negative power supply output side	$V_{VEE2}$	-12	0	V	referenced to GND2
Maximum power supply voltage output side $(V_{VCC2} - V_{VEE2})$	$V_{max2}$	-	28	V	-
Positive power supply input side	$V_{\sf VCC1}$	4.5	5.5	V	_
Pin CLAMP voltage	$V_{CLAMP}$	$V_{VEE2}$	$V_{\sf VCC2}$	V	referenced to GND2
Pin DESAT voltage	$V_{DESAT}$	0	$V_{\sf VCC2}$	V	referenced to GND2
Ambient temperature	$T_{A}$	-40	125	°C	_
Common mode transient immunity	$ DV_{ISO}/dt $	_	50	kV/μs	@ 500 V, <sup>1)</sup>

<sup>1)</sup> The parameter is not subject to production test - verified by design/characterization

### 5.3 Recommended Operating Parameters

Note:

Unless otherwise noted all parameters refer to GND1. The specification for all driver signals is valid for HS and LS with out special notice, e.g. IN+ covers INHS+ as well as INLS+. The signals from driver output side are measured with respect to their specific GND2HS or GND2LS.

Table 4 Recommended Operating Parameters

Parameter	Symbol	Value	Unit	Note / Test Condition
Positive power supply output side	$V_{\sf VCC2}$	15	V	referenced to GND2
Negative power supply output side	$V_{VEE2}$	-8	V	referenced to GND2
Positive power supply input side	$V_{\sf VCC1}$	5	V	referenced to GND1



### **Electrical Parameters**

### 5.4 Electrical Characteristics

Note:

The electrical characteristics involve the spread of values for the supply voltages, load and junction temperatures given below. Typical values represent the median values, which are related to production processes at  $T = 25^{\circ}$ C. Unless otherwise noted all voltages are given with respect to GND. The specification for all driver signals is valid for HS and LS with out special notice, e.g. IN+ covers INHS+ as well as INLS+. The signals from driver output side are measured with respect to their specific GND2HS or GND2LS.

### 5.4.1 Voltage Supply

Table 5 Voltage Supply

Parameter	Symbol	Values			Unit	Note
		Min.	Тур.	Max.		
UVLO Threshold Input	$V_{\mathrm{UVLOH1}}$	_	4.1	4.3	V	_
Chip	$V_{UVLOL1}$	3.5	3.8	_	V	_
	$V_{HYS1}$	0.15	-	-	V	_
UVLO Threshold Output	$V_{\mathrm{UVLOH2}}$	-	12.0	12.6	V	_
Chip	$V_{UVLOL2}$	10.4	11.0	_	V	_
$\overline{ \begin{tabular}{ll} UVLO \ Hysteresis Output \\ Chip \ (V_{\rm UVLOH1} - V_{\rm UVLOL1}) \end{tabular} }$	$V_{HYS2}$	0.7	0.9	-	V	-
Quiescent Current Input Chip	$I_{\mathrm{Q1}}$	-	7	9	mA	V <sub>VCC1</sub> = 5 V IN+ = High, IN- = Low =>OUT = High, RDY = High, /FLT = High
Quiescent Current Output Chip	$I_{\mathrm{Q2}}$	-	4	6	mA	$V_{\text{VCC2}} = 15 \text{ V}$ $V_{\text{VEE2}} = -8 \text{ V}$ $IN+ = \text{High,}$ $IN- = \text{Low}$ $=> \text{OUT} = \text{High,}$ $RDY = \text{High,}$ $/\text{FLT} = \text{High}$

## **Dual IGBT Driver IC**



### **Electrical Parameters**

#### **Logic Input and Output** 5.4.2

Table 6 **Logic Input and Output** 

Parameter	Symbol Values			S	Unit	Note
		Min.	Тур.	Max.		
IN+,IN-, RST Low Input Voltage	$V_{\mathrm{IN+L}}, \ V_{\mathrm{IN-L}}, \ V_{\mathrm{RSTL\#}}$	0	-	1.5	V	-
IN+,IN-, RST High Input Voltage	$V_{\mathrm{IN+H}}, \ V_{\mathrm{IN-H}}, \ V_{\mathrm{RSTH\#}}$	3.5	_	V <sub>VCC1</sub>	V	-
IN-, RST Input Current	$I_{IN ext{-}}, I_{RST ext{\#}}$	_	100	400	μΑ	$\begin{aligned} V_{\text{IN-}} &= \text{GND1} \\ V_{\text{RST\#}} &= \text{GND1} \end{aligned}$
IN+ Input Current	$I_{IN+},$	_	100	400	μΑ	$V_{\text{IN+}} = \text{VCC1}$
RDY,FLT Pull Up Current	$I_{PRDY}, I_{PFLT\#}$	-	100	400	μΑ	$V_{\rm RDY} = {\rm GND1}$ $V_{\rm FLT\#} = {\rm GND1}$
Input Pulse Suppression IN+, IN-	$T_{\text{MININ+}},$ $T_{\text{MININ-}}$	30	40	-	ns	
Input Pulse Suppression RSTfor ENABLE/SHUTDOWN	$T_{MINRST}$	30	40	-	ns	_
Pulse Width RST for Resetting FLT	$T_{RST}$	800	-	-	ns	-
FLT Low Voltage	$V_{FLTL}$	_	_	300	mV	$I_{SINK(FLT\#)} = 5 \text{ mA}$
RDY Low Voltage	$V_{RDYL}$	_	_	300	mV	$I_{SINK(RDY)} = 5 \text{ mA}$

### **Dual IGBT Driver IC**



### **Electrical Parameters**

#### **Gate Driver** 5.4.3

Table 7 **Gate Driver** 

Parameter	Symbol		Values			Note	
		Min.	Тур.	Max.			
High Level Output	$V_{OUTH1}$	V <sub>CC2</sub> -1.2	V <sub>CC2</sub> -0.8	_	٧	I <sub>OUTH</sub> = -20 mA	
Voltage	$V_{OUTH2}$	V <sub>CC2</sub> -2.5	V <sub>CC2</sub> -2.0	-	V	I <sub>OUTH</sub> = -200 mA	
	$V_{OUTH3}$	V <sub>CC2</sub> -9	V <sub>CC2</sub> -5	_	٧	I <sub>OUTH</sub> = -1 A	
	$V_{OUTH4}$		V <sub>CC2</sub> -10	_	٧	$I_{\rm OUTH}$ = -2 A <sup>1)</sup>	
High Level Output Peak Current	$I_{OUTH}$	-1.5	-2.0	_	A	IN+ = High, IN- = Low; OUT = High	
Low Level Output	$V_{OUTL1}$	-	V <sub>VEE2</sub> +0.04	V <sub>VEE2</sub> +0.09	V	I <sub>OUTL</sub> = 20 mA	
Voltage	$V_{OUTL2}$	-	V <sub>VEE2</sub> +0.3	V <sub>VEE2</sub> +0.85	V	I <sub>OUTL</sub> = 200 mA	
	$V_{OUTL3}$	_	V <sub>VEE2</sub> +2.1	$V_{VEE2}$ +5	V	$I_{OUTL} = 1  A$	
	$V_{OUTL4}$	_	V <sub>VEE2</sub> +7	_	٧	$I_{\text{OUTL}} = 2 \text{ A}^{1)}$	
Low Level Output Peak Current	$I_{OUTL}$	1.5	2.0	_	A	IN+ = Low, IN- = Low; OUT = Low, $V_{\text{VCC2}} = 15 \text{ V},$ $V_{\text{VEE2}} = -8 \text{ V}$	

<sup>1)</sup> Not subject to production test. Absolute maximum Ratings are verified by design / characterization

#### **Active Miller Clamp** 5.4.4

Table 8 **Active Miller Clamp** 

Parameter	Symbol		Values	Unit	Note	
		Min.	Тур.	Max.		
Low Level Clamp	$V_{CLAMPL1}$	_	$V_{ m VEE2}$ +0.03	V <sub>VEE2</sub> +0.08	V	$I_{CLAMP}$ = 20 mA
Voltage	$V_{CLAMPL2}$	_	V <sub>VEE2</sub> +0.3	V <sub>VEE2</sub> +0.8	V	$I_{CLAMP}$ = 200 mA
	$V_{CLAMPL3}$	_	$V_{VEE2}$ +1.9	$V_{ m VEE2}$ +4.8	V	$I_{CLAMP} = 1  A$
Low Level Clamp Current	$I_{CLAMPL}$	2	_	-	A	1)
Clamp Threshold Voltage	$V_{CLAMP\_TH}$	1.6	2.1	2.4	V	Related to VEE2

<sup>1)</sup> The parameter is not subject to production test - verified by design/characterization

### **Electrical Parameters**



### 5.4.5 Short Circuit Clamping

Table 9 Short Circuit Clamping

Parameter	Symbol		Values			Note
		Min.	Тур.	Max.		
Clamping voltage (OUT) $(V_{\rm OUT}$ - $V_{\rm VCC2})$	$V_{CLPout}$	-	0.8	1.3	V	IN+ = High, IN- = Low, OUT = High $I_{\text{OUT}}$ = 500 mA pulse test, $t_{\text{CLPmax}}$ = 10 $\mu$ s)
Clamping voltage (CLAMP) ( $V_{\rm VCLAMP}$ - $V_{\rm VCC2}$ )	$V_{CLPclamp}$	-	1.3	-	V	IN+ = High, IN- = Low, OUT = High $I_{CLAMP}$ = 500 mA (pulse test, $t_{CLPmax}$ = 10 $\mu$ s) <sup>1)</sup>
		_	0.7	1.1	V	IN+ = High, IN- = Low, OUT = High $I_{\text{CLAMP}}$ = 20 mA

<sup>1)</sup> Not subject to production test. Absolute maximum Ratings are verified by design / characterization

### **5.4.6** Dynamic Characteristics

Table 10 Dynamic Characteristics<sup>1)</sup>

Parameter	Symbol		Value	S	Unit	Note	
		Min.	Тур.	Max.			
Input IN to output propagation delay ON	$T_{PDON}$	145	170	195	ns	$C_{\rm LOAD}$ = 100 pF $V_{\rm IN+}$ = 50%,	
Input IN to output propagation delay OFF	$T_{PDOFF}$	145	165	190	ns	V <sub>OUT</sub> =50% @ 25°C	
Input IN to output propagation delay distortion $(T_{\text{PDOFF}} - T_{\text{PDON}})$	$T_{ t PDISTO}$	-35	-5	25	ns		
Input IN to output propagation delay ON variation due to temp	$T_{\sf PDONt}$	160	190	220	ns	$C_{\rm LOAD}$ = 100 pF $V_{\rm IN+}$ = 50%, $V_{\rm OUT}$ = 50% @ 125°C	
Input IN to output propagation delay OFF variation due to temp	$T_{PDOFFt}$	165	195	225	ns		
Input IN to output propagation delay distortion $(T_{\text{PDOFF}} - T_{\text{PDON}})$	$T_{ t PDISTOt}$	-25	5	35	ns		

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### **Electrical Parameters**

Table 10 Dynamic Characteristics<sup>1)</sup> (cont'd)

Parameter	Symbol	Values			Unit	Note
		Min.	Тур.	Max.		
Input IN to output propagation delay ON variation due to temp	$T_{PDONt}$	135	165	195	ns	$C_{\rm LOAD}$ = 100 pF $V_{\rm IN+}$ = 50%, $V_{\rm OUT}$ = 50% @ -40°C
Input IN to output propagation delay OFF variation due to temp	$T_{PDOFFt}$	125	155	185	ns	
Input IN to output propagation delay distortion $(T_{\text{PDOFF}} - T_{\text{PDON}})$	$T_{PDISTOt}$	-40	-10	20	ns	
Rise Time	$T_{RISE}$	10	30	60	ns	$C_{\rm LOAD}$ = 1 nF $V_{\rm L}$ 10%, $V_{\rm H}$ 90%
		200	400	800	ns	$C_{\rm LOAD}$ = 34 nF $V_{\rm L}$ 10%, $V_{\rm H}$ 90%
Fall Time	$T_{FALL}$	10	50	90	ns	$C_{\mathrm{LOAD}}$ = 1 nF $V_{\mathrm{L}}$ 10%, $V_{\mathrm{H}}$ 90%
		200	350	600	ns	$C_{\rm LOAD}$ = 34 nF $V_{\rm L}$ 10%, $V_{\rm H}$ 90%

<sup>1)</sup> Measured under the following conditions: V<sub>VCC1</sub>=5V, V<sub>VEE2</sub>=-8V, V<sub>VCC2</sub>=15V

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### **Electrical Parameters**

### **5.4.7** Desaturation Protection

 Table 11
 Desaturation Protection

Parameter	Symbol	Values			Unit	Note
		Min.	Тур.	Max.		
Blanking Capacitor Charge Current	$I_{DESATC}$	450	500	550	μА	$V_{\text{VCC2}} = 15 \text{ V},$ $V_{\text{VEE2}} = -8 \text{ V}$ $V_{\text{DESAT}} = 2 \text{ V}$
Blanking Capacitor Discharge Current	$I_{DESATD}$	9.0	14	-	mA	$\begin{split} &V_{\text{VCC2}} = 15 \text{ V,} \\ &V_{\text{VEE2}} = -8 \text{ V} \\ &V_{\text{DESAT}} = 6 \text{ V} \end{split}$
Desaturation Reference Level	$V_{DESAT\_TH}$	8.3	9	9.5	V	$V_{\rm VCC2}$ = 15 V
Desaturation Filter Time	$T_{DESATfilter}$	_	250	-	ns	$V_{\text{VCC2}} = 15 \text{ V},$ $V_{\text{VEE2}} = -8 \text{ V}$ $V_{\text{DESAT}} = 9 \text{ V}^{1)}$
Desaturation Sense to OUT Low Delay	$T_{\sf DESATOUT}$	_	350	430	ns	$V_{\rm OUT} = 90\%$ $C_{\rm LOAD} = 1~\rm nF$
Desaturation Sense to FLT Low Delay	$T_{DESATFLT}$	_	-	2.25	μs	$V_{\rm FLT\#}$ = 10%; $I_{\rm FLT\#}$ = 5 mA
Desaturation Low Voltage	$V_{DESATL}$	0.4	0.6	0.95	V	IN+=Low, IN-=Low, OUT = Low
Leading edge blanking	$T_{DESATleb}$	_	400	_	ns	1)

<sup>1)</sup> Not subject to production test. This parameter is verified by design / characterization

### 5.4.8 Active Shut Down

Table 12 Active Shut Down

Parameter	Symbol	Values			Unit	Note
		Min.	Тур.	Max.		
Active Shut Down Voltage	$V_{ACTSD}$	-	-	2.0	V	$I_{\rm OUT}$ = -200 mA, $V_{\rm CC2}$ open, referenced to VEE2

### **Insulation Characteristics**



### 6 Insulation Characteristics

Insulation characteristics are guaranteed only within the safety maximum ratings which must be ensured by protective circuits in application. Surface mount classification is class A in accordance with CECCO0802.

This coupler is suitable for "basic insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

### 6.1 Certified according to DIN EN 60747-5-2 (VDE 0884 Teil 2): 2003-01. Basic Insulation

Table 13 According to DIN EN 60747-5-2

Description	Symbol	Characteristics	Unit
Installation classification per EN 60664-1, Table 1			_
for rated mains voltage $\leq$ 150 $V_{\rm RMS}$		I-IV	
for rated mains voltage $\leq$ 300 $V_{\rm RMS}$		1-111	
for rated mains voltage $\leq$ 600 $V_{\rm RMS}$		1-11	
Climatic Classification		55/125/21	_
Pollution Degree (EN 60664-1)		2	-
Minimum External Clearance between input and driver	CLR	8.2	mm
section			
Minimum External Creepage between input and driver	CPG	8.2	mm
section			
Minimum External Clearance between HS- and LS-driver		2.75	mm
output			
Minimum External Creepage between HS- and LS-driver		2.85	mm
output			
Minimum Comparative Tracking Index	СТІ	175	
Maximum Repetitive Insulation Voltage	$V_{IORM}$	1420	$V_{PEAK}$
Highest Allowable Overvoltage	$V_{IOTM}$	6000	$V_{PEAK}$
Maximum Surge Insulation Voltage	$V_{IOSM}$	6000	V

### 6.2 Recognized under UL 1577

Table 14 Recognized under UL 1577

Description	Symbol	Characteristics	Unit
Insulation Withstand Voltage / 1 min	$V_{ISO}$	3750	$V_{rms}$
Insulation Test Voltage / 1 s	$V_{ISO}$	4500	$V_{rms}$

### 6.3 Reliability

For Qualification Report please contact your local Infineon Technologies office.



**Timing Diagrams** 

## 7 Timing Diagrams

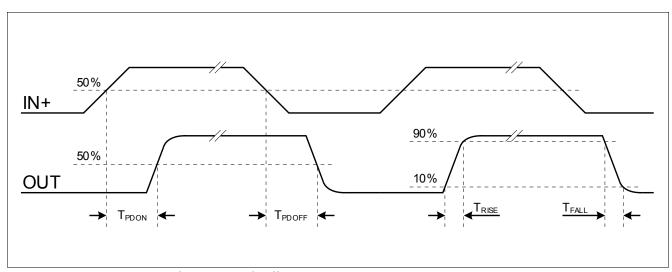


Figure 5 Propagation Delay, Rise and Fall Time

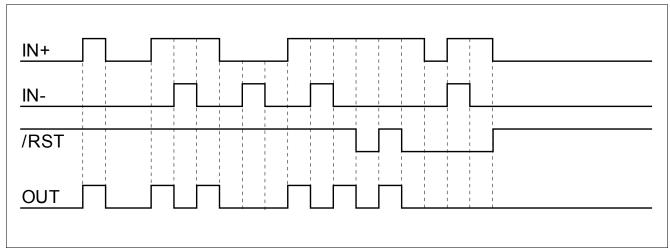


Figure 6 Typical Switching Behavior



### **Timing Diagrams**

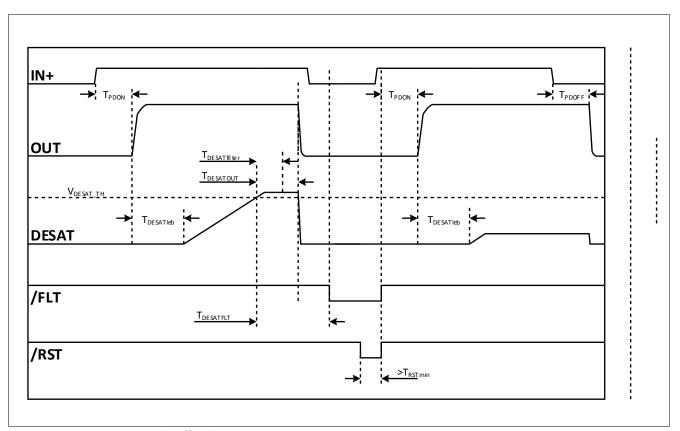


Figure 7 DESAT Switch-Off Behavior

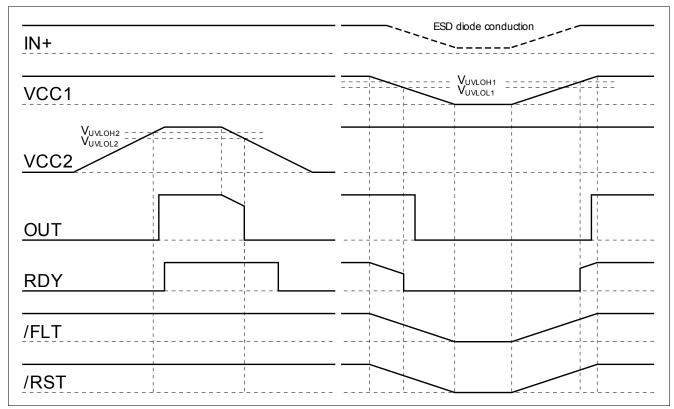


Figure 8 UVLO Behavior

**Package Outlines** 



### 8 Package Outlines

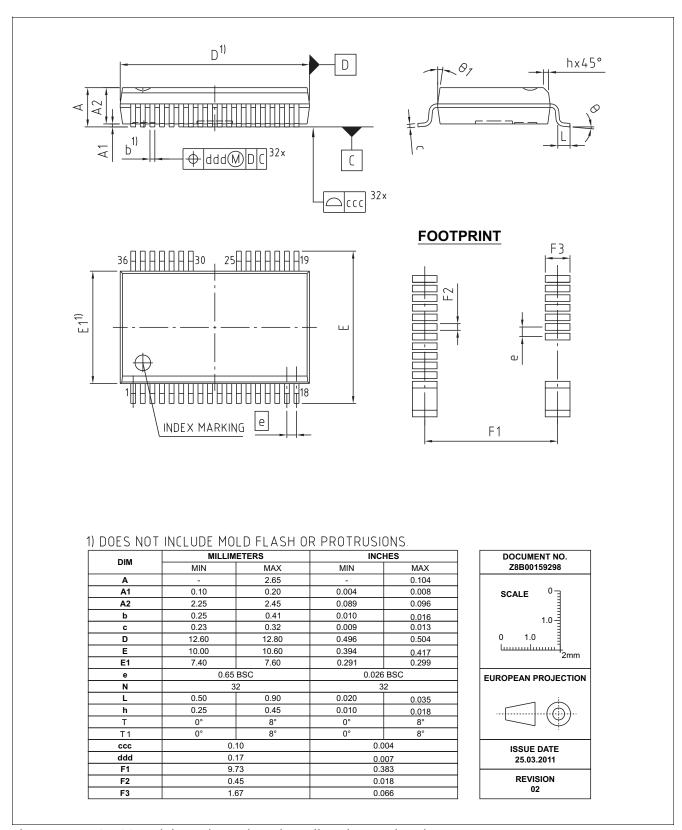


Figure 9 PG-DSO-36 (Plastic (Green) Dual Small Outline Package)



Revision Histor	у			
Page or Item	Subjects (major changes since previous revision)			
Rev 3.1, 2016-0	4-05			
Rev 3.0, 2015-1	1-27			
All	Update latest template			
Page 7	Removed Figure 1 "Typical Application".			
Page 5	Updated Figure 1.			
Page 7	Updated INHS+ and INLS+ description.			
Page 8	Updated INHS- and INLS- description.			
Page 14	Updated Table 2.			
Page 16	Updated Table 3.			
Page 18	Updated Table 6.			
Page 19	Updated Table 7 (added footnote).			
Page 20	Updated Table 9 (added footnote).			

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